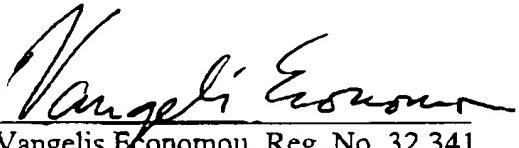


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APIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Sang Ick LEE et al. ] Group Art Unit: 2823  
] ]  
] Examiner: Pham, Thanh V.  
Serial No.: 09/994,284 ]  
] AMENDMENT AFTER FINAL  
Filed: 26 November 2001 ]  
] EXPEDITED PROCEDURE  
For: METHOD OF FORMING METAL ]  
GATE IN SEMICONDUCTOR ]  
DEVICE ]

Certification under 37 C.F.R. §1.8(a)

I hereby certify that this correspondence, and all documents referred to herein as being attached, are being transmitted by facsimile to the United States Patent and Trademark Office at the following facsimile number: (703) 308-7382, to the attention of Examiner Pham, and addressed to the Commissioner for Patents, Washington, D.C. 20231 on December 13, 2002.

  
Vangelis Economou, Reg. No. 32,341

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE UNDER 37 C.F.R. §1.116

In response to the Office Action dated October 15, 2002, please consider the following:

REMARKS

Reconsideration is respectfully requested.

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